

ABSTRACT

Chemical mechanical planarization of surfaces of copper, tantalum and tantalum  
5 nitride is accomplished by means of the chemical formulations of the present  
invention. The chemical formulations may optionally include abrasive particles  
and which may be chemically reactive or inert. Contact or noncontact CMP may  
be performed with the present chemical formulations. Substantially 1:1 removal  
rate selectivity for Cu and Ta/TaN is achieved.

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